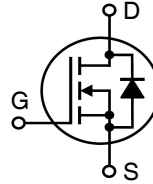


# X2-Class HiPerFET™ Power MOSFET

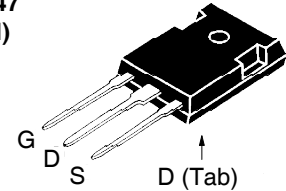
## IXFH80N65X2 IXFK80N65X2

$V_{DSS} = 650V$   
 $I_{D25} = 80A$   
 $R_{DS(on)} \leq 38m\Omega$

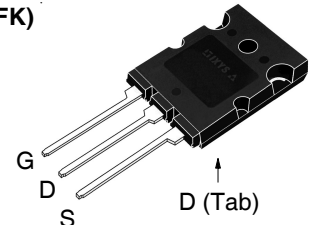
N-Channel Enhancement Mode  
 Avalanche Rated  
 Fast Intrinsic Diode



TO-247  
(IXFH)



TO-264  
(IXFK)



G = Gate      D = Drain  
 S = Source    Tab = Drain

| Symbol     | Test Conditions  | Maximum Ratings |            |
|------------|--|-----------------|------------|
| $V_{DSS}$  | $T_J = 25^\circ C$ to $150^\circ C$                                | 650             | V          |
| $V_{DGR}$  | $T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$          | 650             | V          |
| $V_{GSS}$  | Continuous   | $\pm 30$        | V          |
| $V_{GSM}$  | Transient  | $\pm 40$        | V          |
| $I_{D25}$  | $T_C = 25^\circ C$   | 80              | A          |
| $I_{DM}$   | $T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$               | 160             | A          |
| $I_A$      | $T_C = 25^\circ C$   | 20              | A          |
| $E_{AS}$   | $T_C = 25^\circ C$   | 3               | J          |
| $dv/dt$    | $I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$ | 50              | V/ns       |
| $P_D$      | $T_C = 25^\circ C$   | 890             | W          |
| $T_J$      |  | -55 ... +150    | $^\circ C$ |
| $T_{JM}$   |  | 150             | $^\circ C$ |
| $T_{stg}$  |  | -55 ... +150    | $^\circ C$ |
| $T_L$      | Maximum Lead Temperature for Soldering                             | 300             | $^\circ C$ |
| $T_{SOLD}$ | 1.6 mm (0.062in.) from Case for 10s                                | 260             | $^\circ C$ |
| $M_d$      | Mounting Torque  | 1.13 / 10       | Nm/lb.in   |
| Weight     | TO-247   | 6               | g          |
|            | TO-264   | 10              | g          |

### Features

- International Standard Packages
- Low  $R_{DS(ON)}$  and  $Q_G$
- Avalanche Rated
- Low Package Inductance

### Advantages

- High Power Density
- Easy to Mount
- Space Savings

### Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

| Symbol       | Test Conditions<br>( $T_J = 25^\circ C$ , Unless Otherwise Specified) | Characteristic Values |      |                    |
|--------------|---|-----------------------|------|--------------------|
|              |   | Min.                  | Typ. | Max.               |
| $BV_{DSS}$   | $V_{GS} = 0V$ , $I_D = 1mA$   | 650                   |      | V                  |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 4mA$                                       | 3.5                   |      | 5.0 V              |
| $I_{GSS}$    | $V_{GS} = \pm 30V$ , $V_{DS} = 0V$                                    |                       |      | $\pm 100$ nA       |
| $I_{DSS}$    | $V_{DS} = V_{DSS}$ , $V_{GS} = 0V$<br>$T_J = 125^\circ C$             |                       |      | 50 $\mu A$<br>3 mA |
| $R_{DS(on)}$ | $V_{GS} = 10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1                   |                       |      | 38 m $\Omega$      |

| Symbol                              | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)                                      | Characteristic Values                                  |      |                         |
|-------------------------------------|--|--|------|-------------------------|
|                                     |  | Min.   | Typ. | Max                     |
| $g_{fs}$                            | $V_{DS} = 10\text{V}$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1   | 33   | 55   | S                       |
| $R_{Gi}$                            | Gate Input Resistance  |  | 0.6  | $\Omega$                |
| $C_{iss}$                           | } $V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$   |  | 8300 | pF                      |
| $C_{oss}$                           |  |  | 5010 | pF                      |
| $C_{rss}$                           |  |  | 1.6  | pF                      |
| <b>Effective Output Capacitance</b> |  |  |      |                         |
| $C_{o(er)}$                         | Energy related   | } $V_{GS} = 0\text{V}$<br>$V_{DS} = 0.8 \cdot V_{DSS}$ | 280  | pF                      |
| $C_{o(tr)}$                         | Time related   |  | 1160 | pF                      |
| <b>Resistive Switching Times</b>    |  |  |      |                         |
| $t_{d(on)}$                         | } $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$<br>$R_G = 3\Omega$ (External) |  | 32   | ns                      |
| $t_r$                               |  |  | 24   | ns                      |
| $t_{d(off)}$                        |  |  | 70   | ns                      |
| $t_f$                               |  |  | 11   | ns                      |
| $Q_{g(on)}$                         | } $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$                               |  | 140  | nC                      |
| $Q_{gs}$                            |  |  | 50   | nC                      |
| $Q_{gd}$                            |  |  | 40   | nC                      |
| $R_{thJC}$                          |  |  |      | 0.14 $^\circ\text{C/W}$ |
| $R_{thCS}$                          | TO-247   |  | 0.21 | $^\circ\text{C/W}$      |
|                                     | TO-264   |  | 0.15 | $^\circ\text{C/W}$      |

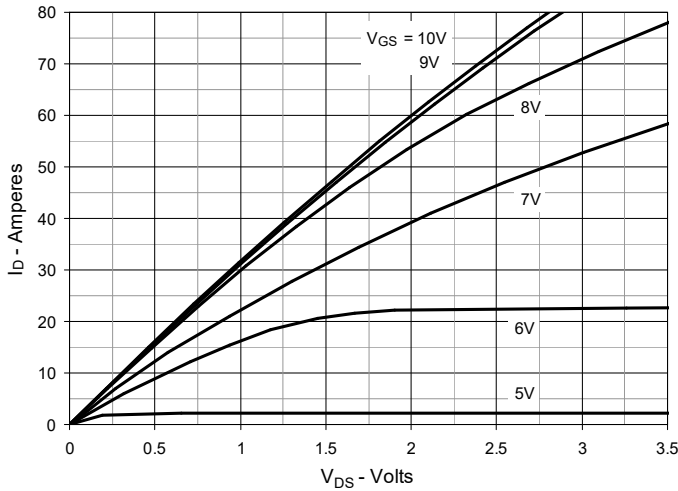
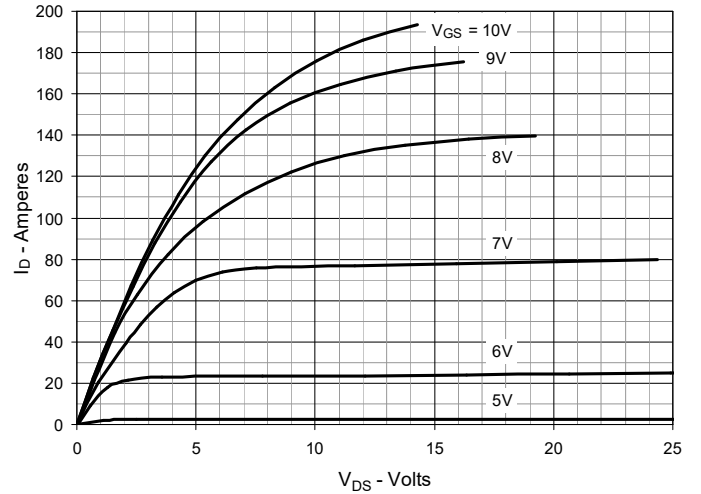
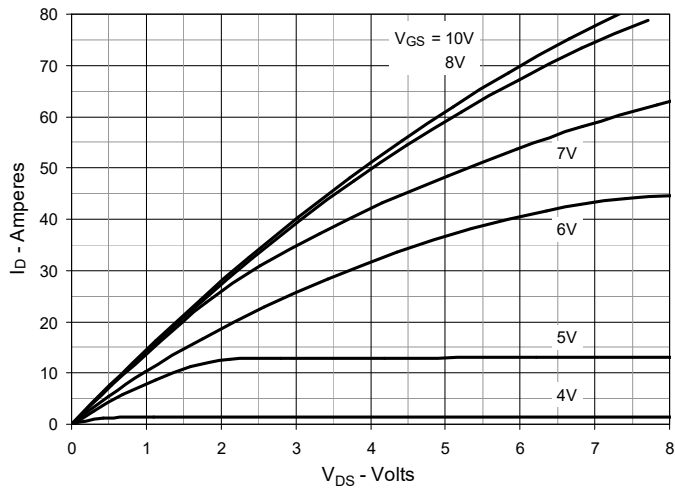
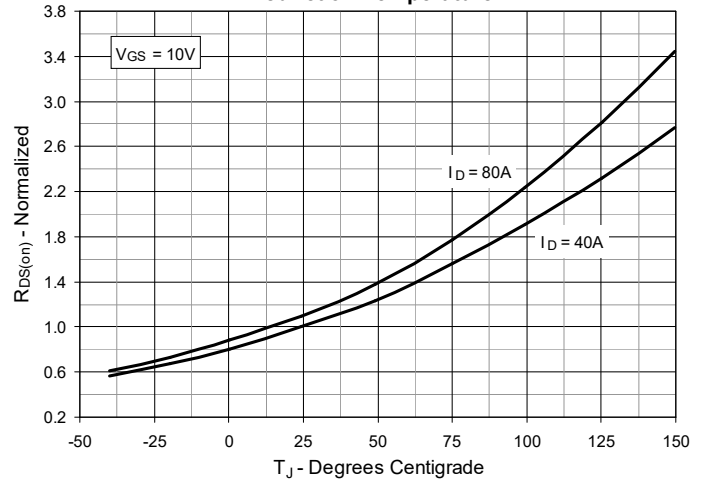
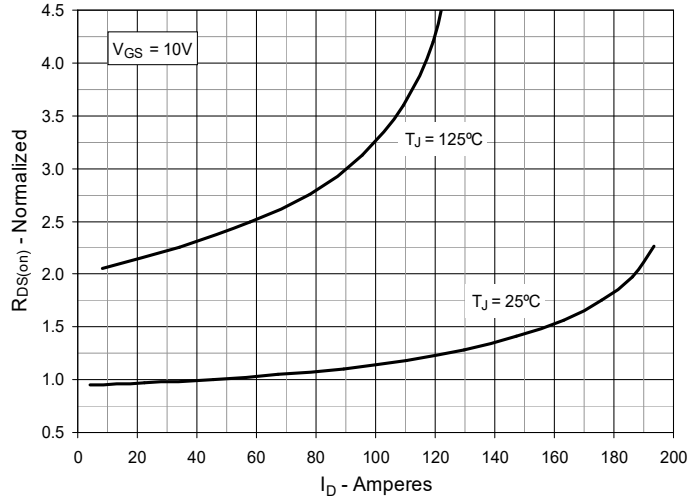
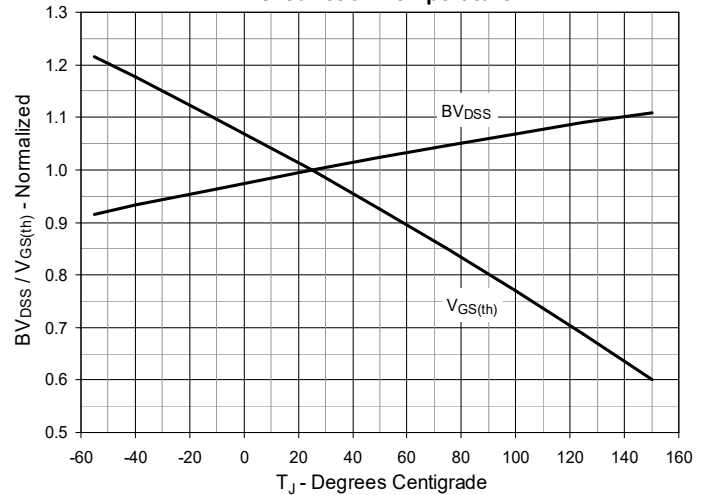
**Source-Drain Diode**

| Symbol   | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)      | Characteristic Values |      |               |
|----------|--|-----------------------|------|---------------|
|          |  | Min.                  | Typ. | Max           |
| $I_S$    | $V_{GS} = 0\text{V}$   |                       |      | 80 A          |
| $I_{SM}$ | Repetitive, pulse Width Limited by $T_{JM}$                                      |                       |      | 320 A         |
| $V_{SD}$ | $I_F = I_S$ , $V_{GS} = 0\text{V}$ , Note 1                                      |                       |      | 1.4 V         |
| $t_{rr}$ | } $I_F = 40\text{A}$ , $-di/dt = 100\text{A}/\mu\text{s}$<br>$V_R = 100\text{V}$ |                       | 200  | ns            |
| $Q_{RM}$ |  |                       | 1.7  | $\mu\text{C}$ |
| $I_{RM}$ |  |                       | 16.7 | A             |

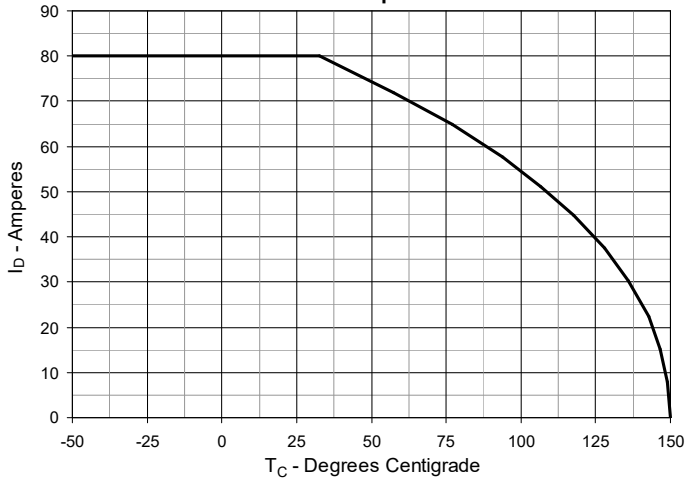
Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

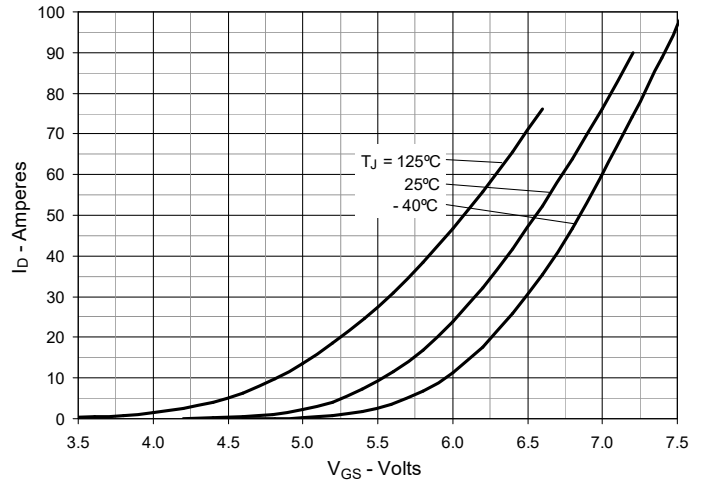
|  |           |           |           |           |             |             |             |             |             |             |
|--|-----------|-----------|-----------|-----------|-------------|-------------|-------------|-------------|-------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665   | 6,404,065B1 | 6,683,344   | 6,727,585   | 7,005,734B2 | 7,157,338B2 |
|  | 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123B1 | 6,534,343   | 6,710,405B2 | 6,759,692   | 7,063,975B2 |             |
|  | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728B1 | 6,583,505   | 6,710,463   | 6,771,478B2 | 7,071,537   |             |

**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$** 

**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 40\text{A}$  Value vs. Junction Temperature**

**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 40\text{A}$  Value vs. Drain Current**

**Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature**


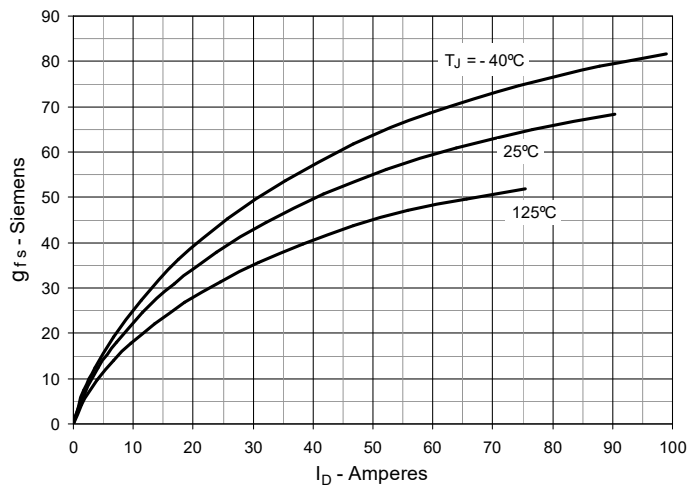
**Fig. 7. Maximum Drain Current vs. Case Temperature**



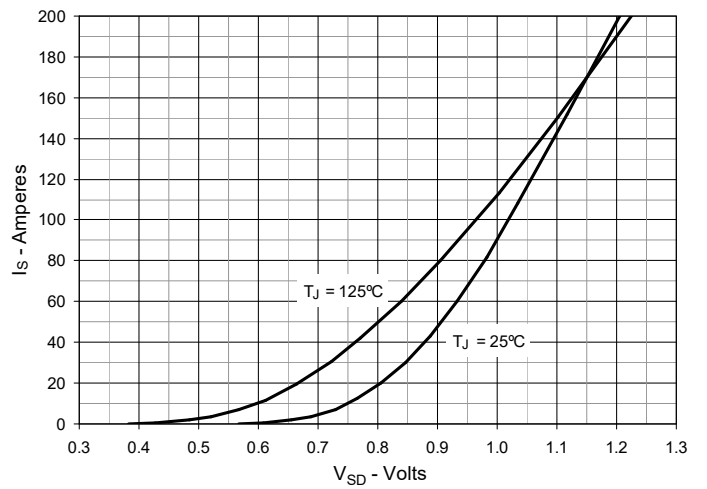
**Fig. 8. Input Admittance**



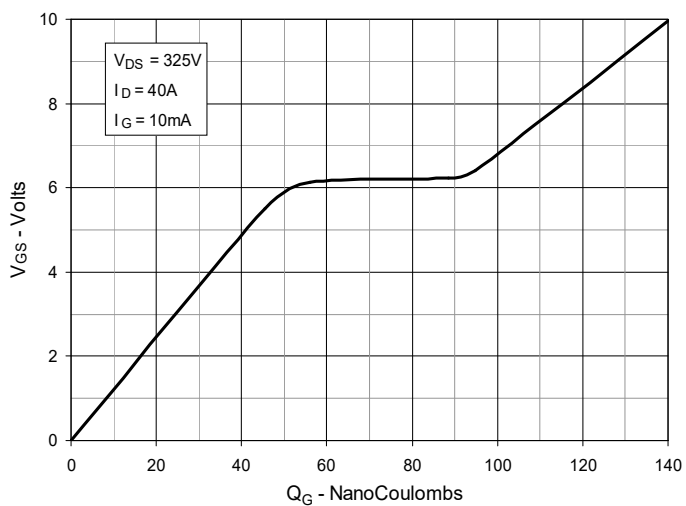
**Fig. 9. Transconductance**



**Fig. 10. Forward Voltage Drop of Intrinsic Diode**



**Fig. 11. Gate Charge**



**Fig. 12. Capacitance**

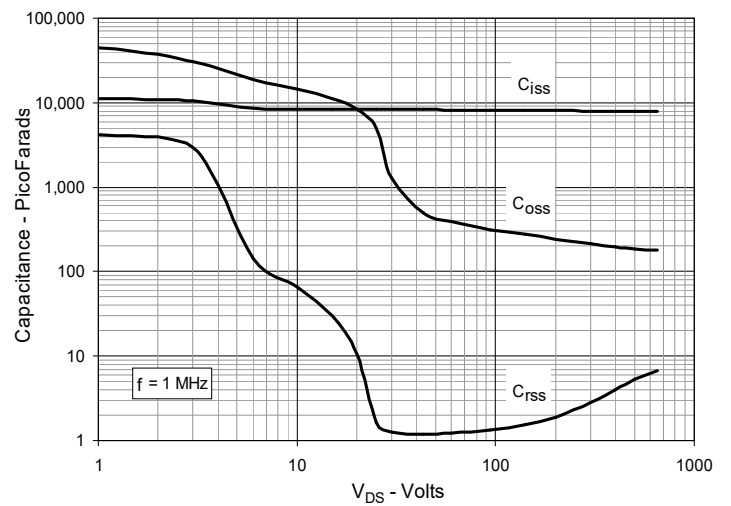


Fig. 13. Output Capacitance Stored Energy

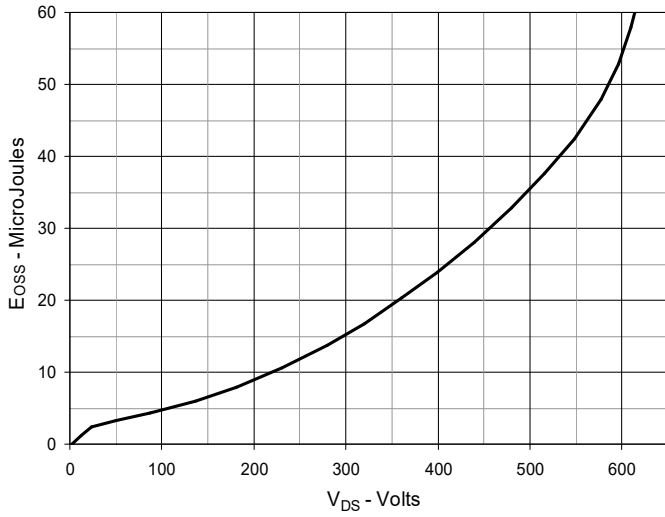


Fig. 14. Forward-Bias Safe Operating Area

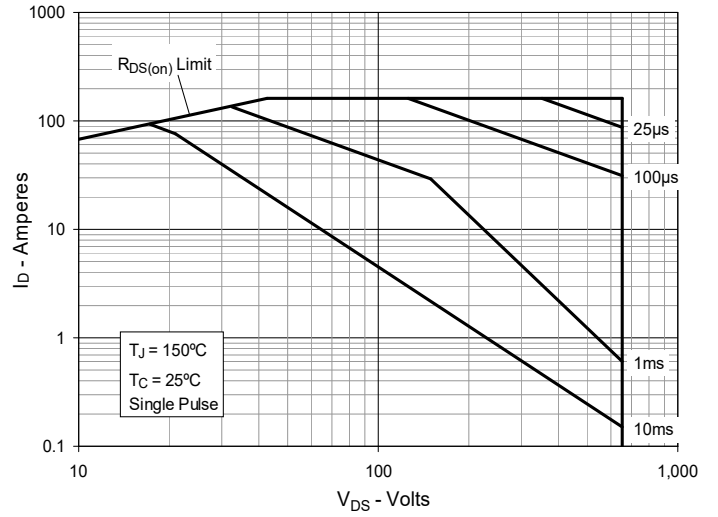
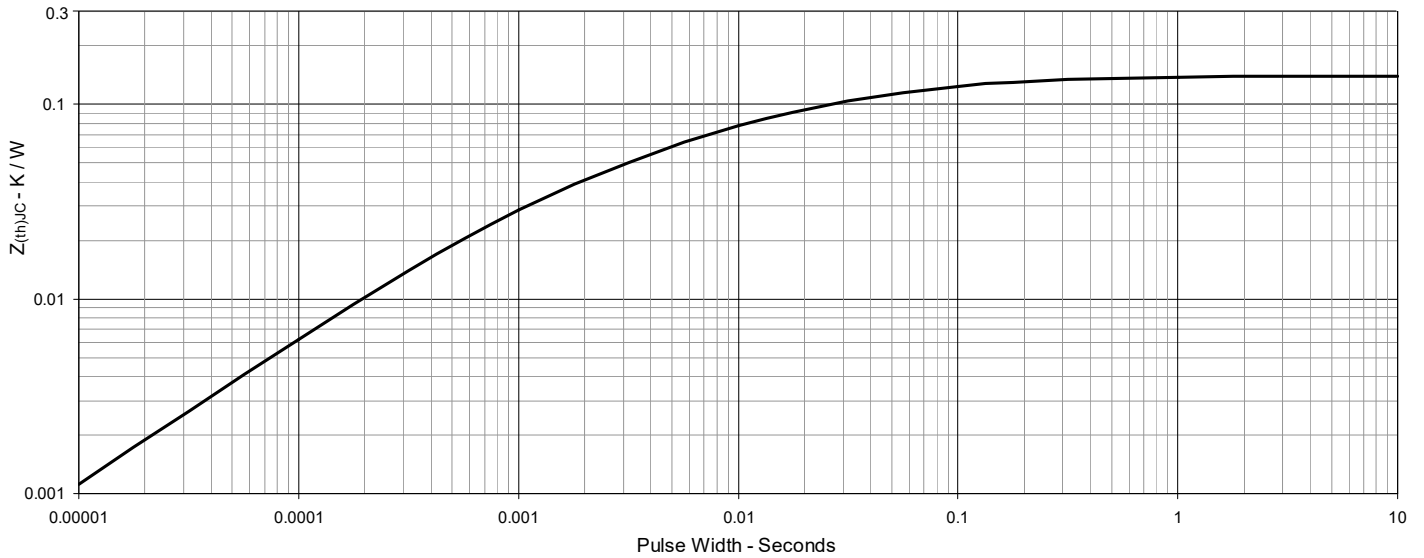
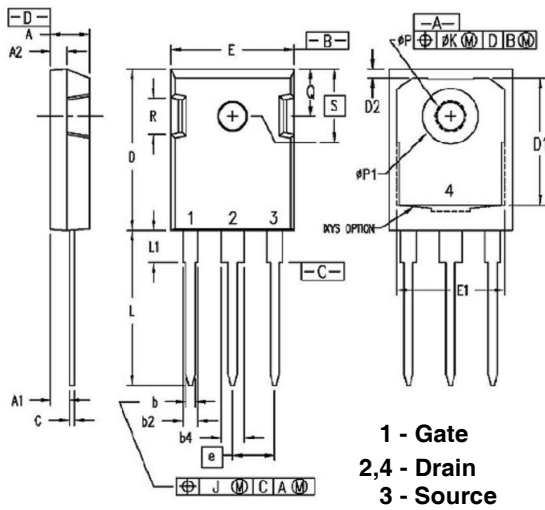


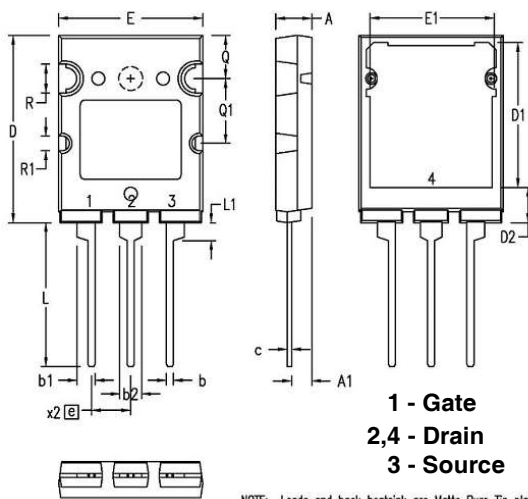
Fig. 15. Maximum Transient Thermal Impedance



**TO-247 Outline**


| SYM | INCHES   |      | MILLIMETERS |       |
|-----|----------|------|-------------|-------|
|     | MIN      | MAX  | MIN         | MAX   |
| A   | .190     | .205 | 4.83        | 5.21  |
| A1  | .090     | .100 | 2.29        | 2.54  |
| A2  | .075     | .085 | 1.91        | 2.16  |
| b   | .045     | .055 | 1.14        | 1.40  |
| b2  | .075     | .087 | 1.91        | 2.20  |
| b4  | .115     | .126 | 2.92        | 3.20  |
| C   | .024     | .031 | 0.61        | 0.80  |
| D   | .819     | .840 | 20.80       | 21.34 |
| D1  | .650     | .690 | 16.51       | 17.53 |
| D2  | .035     | .050 | 0.89        | 1.27  |
| E   | .620     | .635 | 15.75       | 16.13 |
| E1  | .545     | .565 | 13.84       | 14.35 |
| e   | .215 BSC |      | 5.45 BSC    |       |
| J   | --       | .010 | --          | 0.25  |
| K   | --       | .025 | --          | 0.64  |
| L   | .780     | .810 | 19.81       | 20.57 |
| L1  | .150     | .170 | 3.81        | 4.32  |
| øP  | .140     | .144 | 3.55        | 3.65  |
| øP1 | .275     | .290 | 6.99        | 7.37  |
| Q   | .220     | .244 | 5.59        | 6.20  |
| R   | .170     | .190 | 4.32        | 4.83  |
| S   | .242 BSC |      | 6.15 BSC    |       |

NOTE: This drawing will meet all dimensions requirement of JEDEC outlines TO-247 AD (R-PSIP-F3)

**TO-264 Outline**


| SYM | INCHES   |       | MILLIMETERS |       |
|-----|----------|-------|-------------|-------|
|     | MIN      | MAX   | MIN         | MAX   |
| A   | .185     | .209  | 4.70        | 5.30  |
| A1  | .102     | .118  | 2.60        | 3.00  |
| b   | .035     | .049  | 0.90        | 1.25  |
| b1  | .091     | .106  | 2.30        | 2.70  |
| b2  | .110     | .126  | 2.80        | 3.20  |
| c   | .020     | .033  | 0.50        | 0.85  |
| D   | 1.012    | 1.035 | 25.70       | 26.30 |
| D1  | .783     | .799  | 19.90       | 20.30 |
| D2  | .185     | .205  | 4.70        | 5.20  |
| E   | .776     | .799  | 19.70       | 20.30 |
| E1  | .661     | .677  | 16.80       | 17.20 |
| e   | .215 BSC |       | 5.46 BSC    |       |
| L   | .768     | .807  | 19.50       | 20.50 |
| L1  | .091     | .106  | 2.30        | 2.70  |
| Q   | .228     | .244  | 5.80        | 6.20  |
| Q1  | .346     | .362  | 8.80        | 9.20  |
| øR  | .150     | .165  | 3.80        | 4.20  |
| øR1 | .071     | .087  | 1.80        | 2.20  |

NOTE: Leads and back heatsink are Matte Pure Tin plated.



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